

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for manufacturing ceramics comprising a step of forming a ceramic film on a substrate by mixing a fine particle of a raw material species which becomes at least part of raw materials for ceramics with an active species having high kinetic energy, and feeding the mixed fine particle and active species to the substrate so that the fine particles of the raw material species are deposited on the substrate while being provided with kinetic energy from the active species and the migration energy of atoms in the film is increased by providing energy to the fine particles of the raw material species by the active species, wherein the ceramic film is formed by an LSMCD process or a misted CVD process.
2. (Original) The method for manufacturing ceramics according to claim 1, wherein a diameter of the fine particle is 0.1 μm or less.
3. (Original) The method for manufacturing ceramics according to claim 1, wherein a diameter of the fine particle is 0.01 μm or less.
4. (Original) The method for manufacturing ceramics according to claim 1, wherein the fine particle is electrically charged.
5. (Original) The method for manufacturing ceramics according to claim 1, wherein the fine particle of the raw material species is gasified before being mixed with the active species.
6. (Original) The method for manufacturing ceramics according to claim 1, wherein the active species is a radical or an ion.

7. (Original) The method for manufacturing ceramics according to claim 6, wherein the active species is a radical or an ion of the raw material species which becomes part of the raw materials for ceramics.

8. (Original) The method for manufacturing ceramics according to claim 6, wherein the active species is a radical or an ion of oxygen or nitrogen.

9. (Original) The method for manufacturing ceramics according to claim 6, wherein the active species is an ion obtained by activating inert gas.

10. (Original) The method for manufacturing ceramics according to claim 9, wherein the inert gas is an ion of argon or xenon.

11. (Original) The method for manufacturing ceramics according to claim 1, wherein at least the active species is fed to the substrate in an accelerated state.

12. (Previously Amended) The method for manufacturing ceramics according to claim 1, wherein the ceramic film is formed on a partial portion of the substrate.

13. (Original) The method for manufacturing ceramics according to claim 12, further comprising a step of forming a film-forming region having affinity to ceramics to be formed, and a non-film-forming region having no affinity to the ceramics to be formed, thereby self-alignably forming a ceramic film in the film-forming region.

14. Canceled.

15. (Original) The method for manufacturing ceramics according to claim 1, wherein the ceramic film is a dielectric.

16. (Original) The method for manufacturing ceramics according to claim 15, wherein the dielectric is formed at a temperature of 600°C or less.

17. (Original) The method for manufacturing ceramics according to claim 15, wherein the dielectric is formed at a temperature of 450°C or less.

18-33. (Canceled)